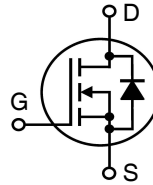


**Q3-Class  
HiperFET™  
Power MOSFET**

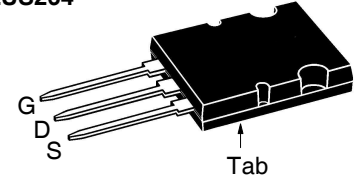
**IXFB62N80Q3**

**V<sub>DSS</sub> = 800V**  
**I<sub>D25</sub> = 62A**  
**R<sub>DS(on)</sub> ≤ 140mΩ**  
**t<sub>rr</sub> ≤ 300ns**

N-Channel Enhancement Mode  
 Fast Intrinsic Rectifier  
 Avalanche Rated



**PLUS264™**



G = Gate      D = Drain  
 S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	800	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C, R <sub>GS</sub> = 1MΩ	800	V
V <sub>GSS</sub>	Continuous	±30	V
V <sub>GSM</sub>	Transient	±40	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	62	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, Pulse Width Limited by T <sub>JM</sub>	180	A
I <sub>A</sub>	T <sub>C</sub> = 25°C	62	A
E <sub>AS</sub>	T <sub>C</sub> = 25°C	5	J
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C	50	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	1560	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering	300	°C
T <sub>SOLD</sub>	1.6 mm (0.062in.) from Case for 10s	260	°C
F <sub>C</sub>	Mounting Force	30..120/6.7..27	N/lb.
Weight		10	g

**Features**

- Low Intrinsic Gate Resistance
- Low Package Inductance
- Avalanche Rated
- Fast Intrinsic Rectifier
- Low R<sub>DS(on)</sub> and Q<sub>G</sub>

**Advantages**

- High Power Density
- Easy to Mount
- Space Savings

**Applications**

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- Temperature and Lighting Controls

Symbol	Test Conditions (T <sub>J</sub> = 25°C Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 3mA	800		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 8mA	3.5		6.5 V
I <sub>GSS</sub>	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0V			±200 nA
I <sub>DSS</sub>	V <sub>DS</sub> = 0.8 • V <sub>DSS</sub> , V <sub>GS</sub> = 0V T <sub>J</sub> = 125°C			50 μA 4 mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1			140 mΩ

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{V}, I_D = I_D = 0.5 \cdot I_{D25}$ , Note 1	28	48	S
$C_{iss}$ $C_{oss}$ $C_{rss}$	} $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		13.6	nF
			1260	pF
			100	pF
$R_{Gi}$	Gate Input Resistance		0.13	$\Omega$
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	} <b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		54	ns
			20	ns
			62	ns
			11	ns
$Q_{g(on)}$ $Q_{gs}$ $Q_{gd}$	} $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = I_D = 0.5 \cdot I_{D25}$		270	nC
			90	nC
			120	nC
$R_{thJC}$ $R_{thCS}$				0.08 $^\circ\text{C/W}$ 0.13 $^\circ\text{C/W}$

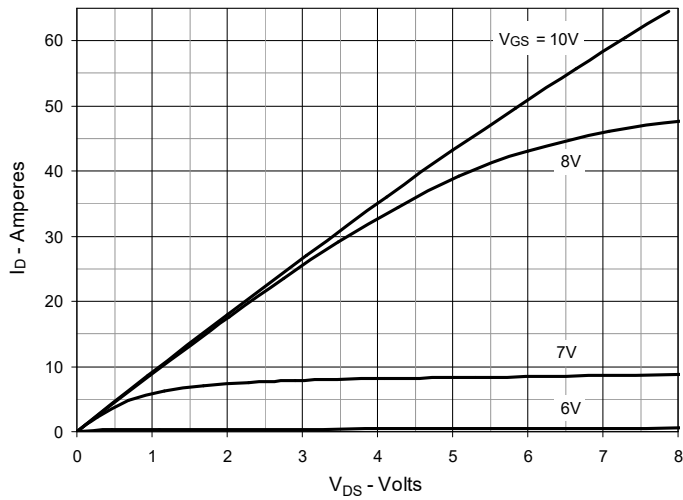
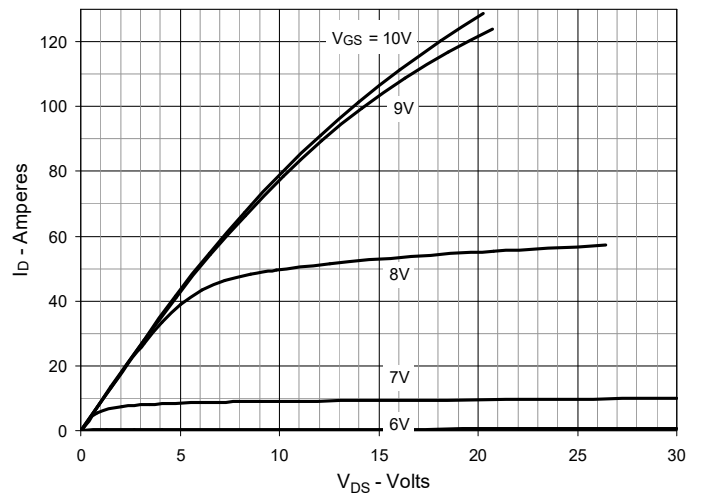
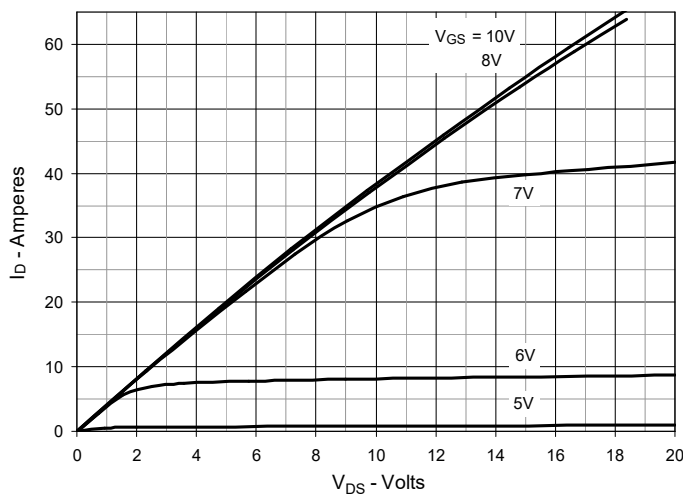
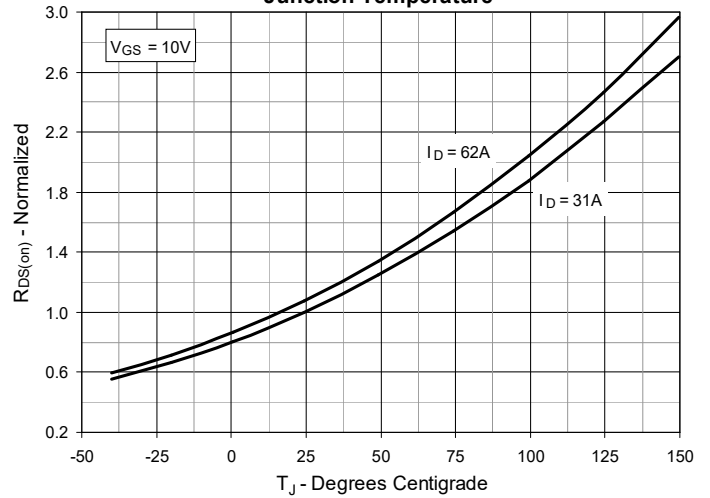
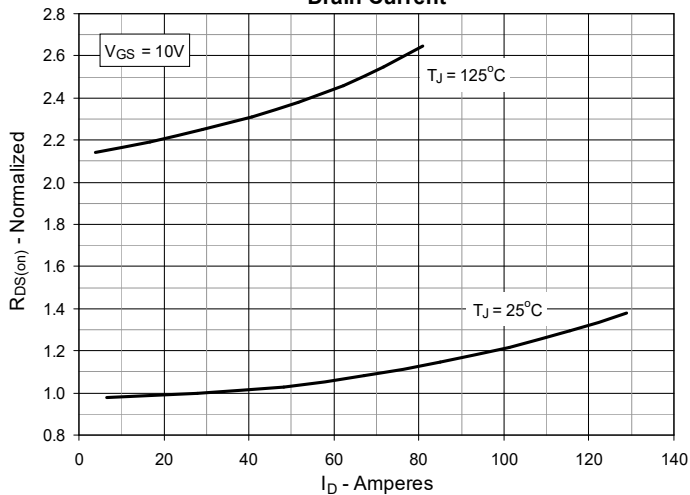
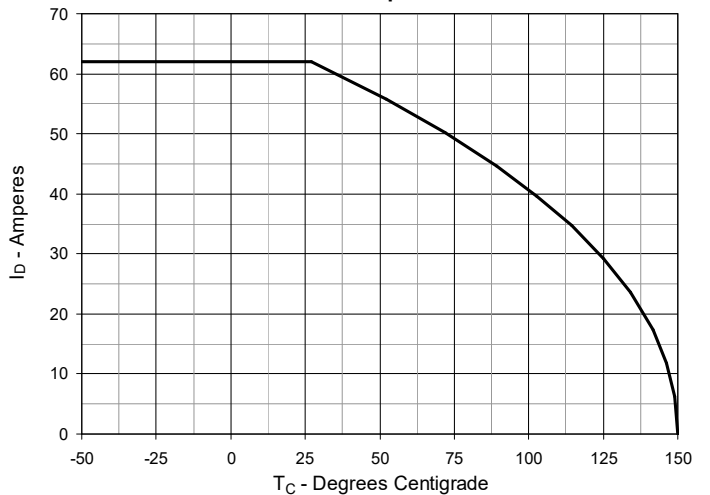
**Source-Drain Diode**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			62 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			250 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$ $Q_{RM}$ $I_{RM}$	} $I_F = 31\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
			1.6	$\mu\text{C}$
			13.4	A

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 31\text{A}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 31\text{A}$  Value vs. Drain Current**

**Fig. 6. Maximum Drain Current vs. Case Temperature**


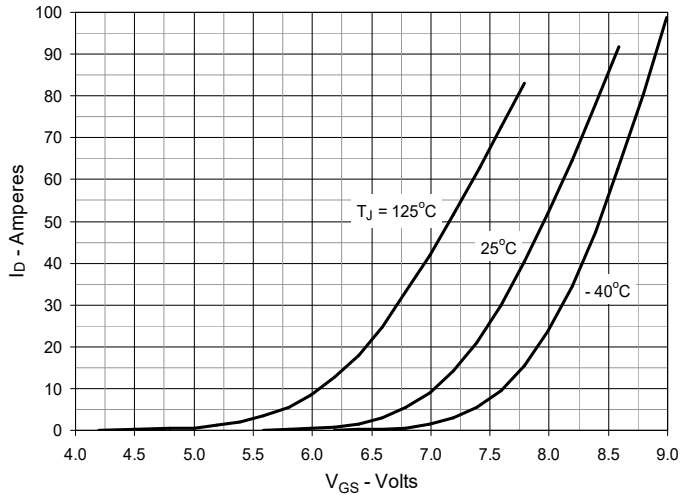
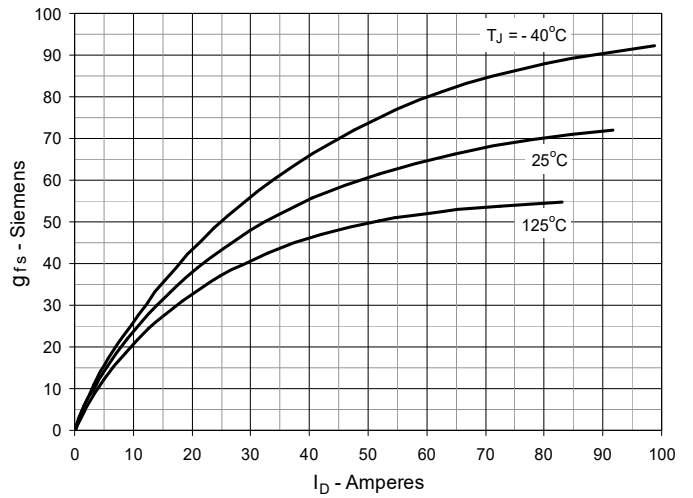
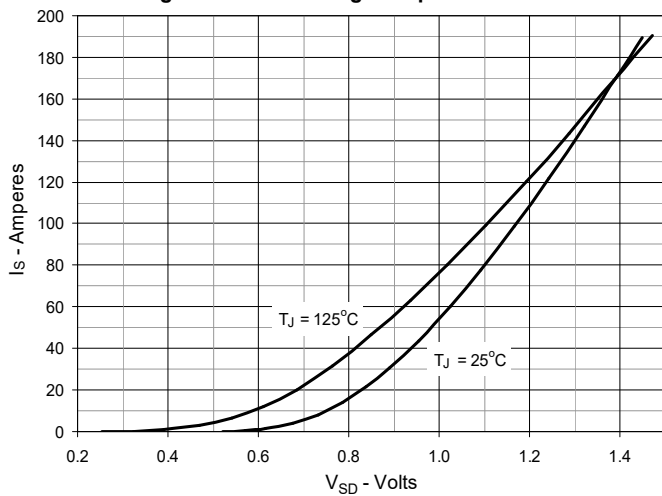
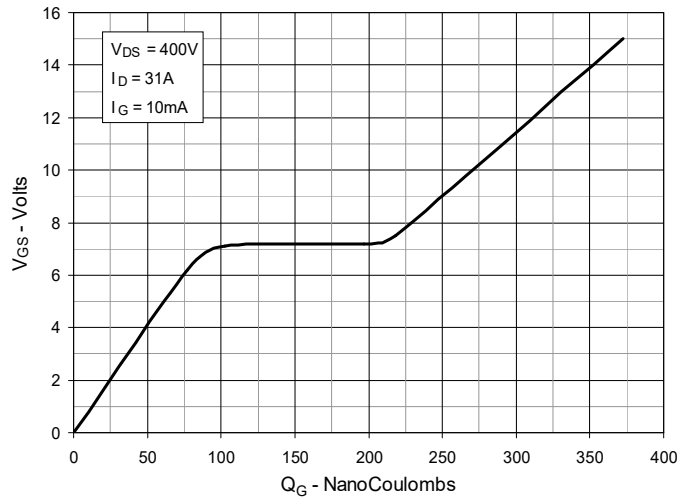
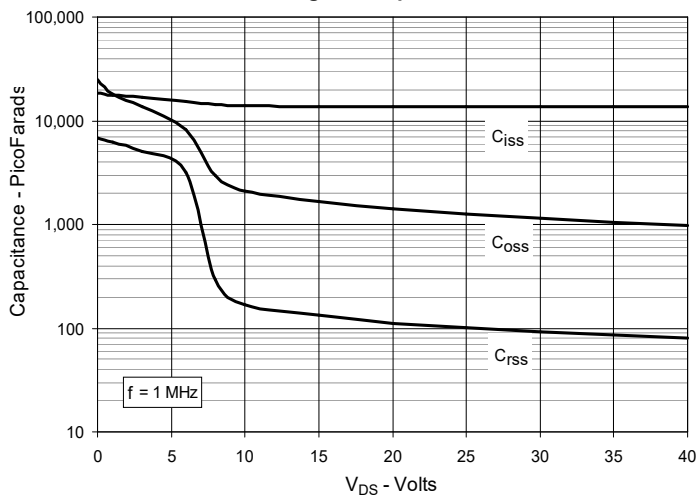
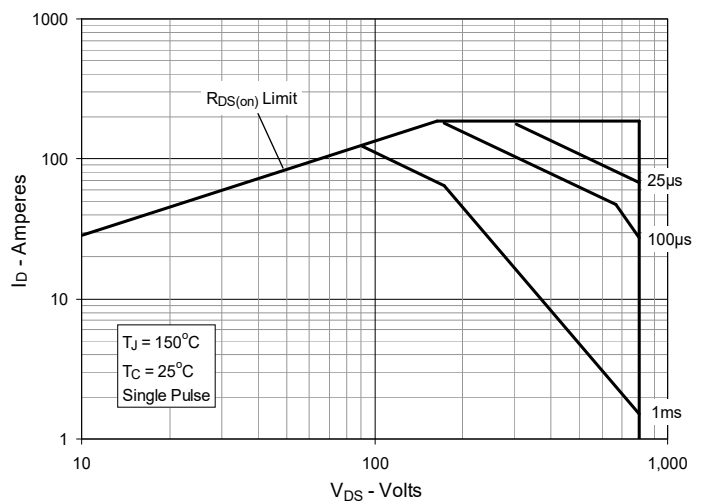
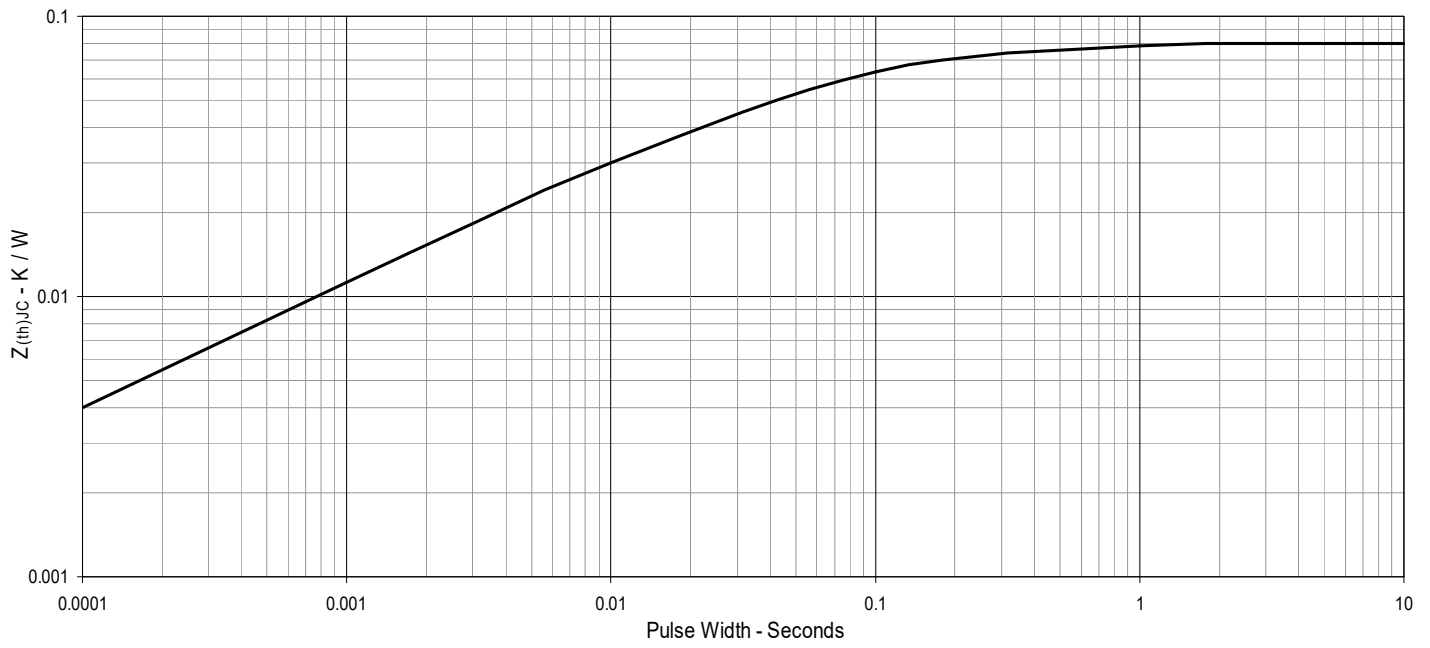
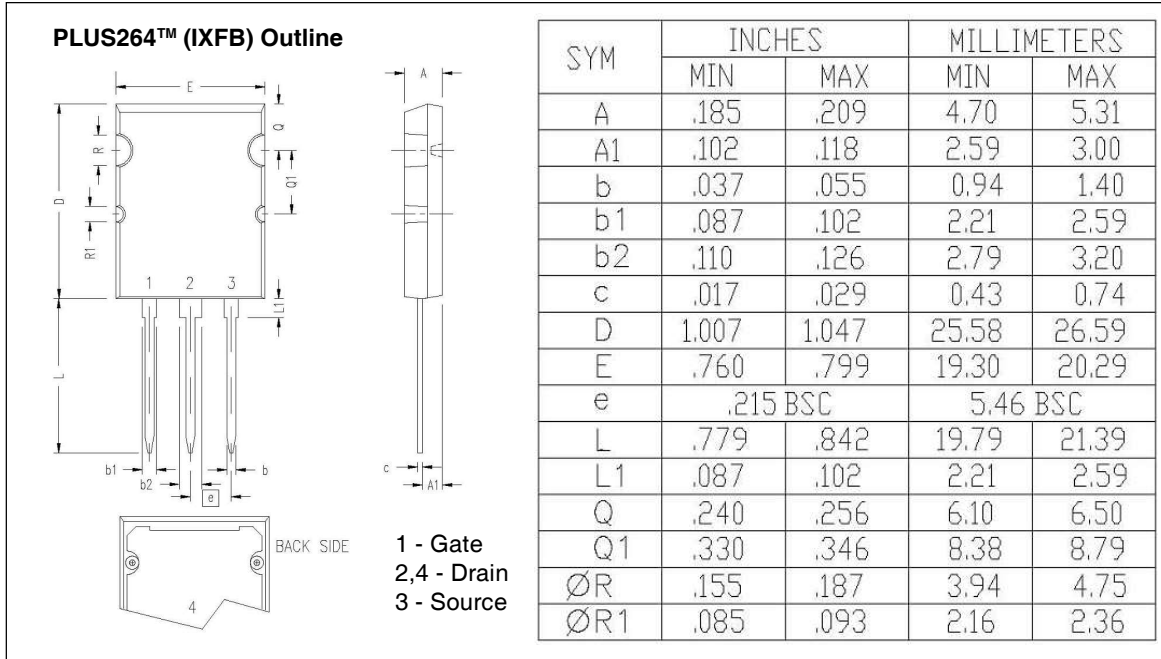
**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Forward-Bias Safe Operating Area**


Fig. 13. Maximum Transient Thermal Impedance







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